

## CSD23280F3 -12V P 沟道 FemtoFET™ MOSFET

### 1 特性

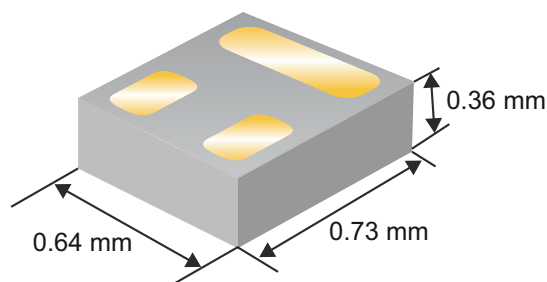
- 低导通电阻
- 超低  $Q_g$  和  $Q_{gd}$
- 高漏极工作电流
- 超小尺寸
  - 0.73mm × 0.64mm
- 超薄型封装
  - 最大厚度为 0.36mm
- 集成型 ESD 保护二极管
  - 额定值 > 4kV HBM
  - 额定值 > 2kV CDM
- 无铅且无卤素
- 符合 RoHS

### 2 应用

- 针对负载开关应用进行了优化
- 针对通用开关应用进行了优化
- 电池应用
- 手持式和移动类应用

### 3 说明

该-12V、97mΩ P 沟道 FemtoFET™ MOSFET 经过设计和优化，能够最大限度地减小在许多手持式和移动应用中占用的空间。这项技术能够在替代标准小信号 MOSFET 的同时大幅减小封装尺寸。



典型器件尺寸

### 产品概要

$T_A = 25^\circ\text{C}$		典型值	单位
$V_{DS}$	漏源电压	- 12	V
$Q_g$	栅极电荷总量 (4.5V)	0.95	nC
$Q_{gd}$	栅极电荷 (栅极到漏极)	0.068	nC
$R_{DS(on)}$	漏源导通电阻	$V_{GS} = -1.5\text{V}$	230
		$V_{GS} = -1.8\text{V}$	180
		$V_{GS} = -2.5\text{V}$	129
		$V_{GS} = -4.5\text{V}$	97
$V_{GS(th)}$	阈值电压	- 0.65	V

### 器件信息(1)

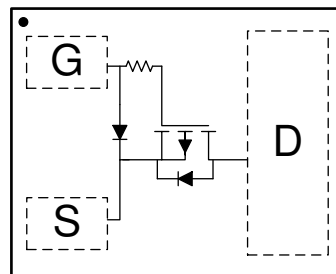
器件	数量	介质	封装	配送
CSD23280F3	3000	7 英寸卷带	Femto 0.73mm × 0.64mm 基板栅格阵列 (LGA)	卷带包装
CSD23280F3T	250			

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

### 绝对最大额定值

$T_A = 25^\circ\text{C}$		值	单位
$V_{DS}$	漏源电压	- 12	V
$V_{GS}$	栅源电压	- 6	V
$I_D$	持续漏极电流(1)	2.9	A
	持续漏极电流(2)	1.8	
$I_{DM}$	脉冲漏极电流(1) (3)	11.4	A
$P_D$	功率耗散(1)	1.4	W
	功率耗散(2)	0.5	
$V_{(ESD)}$	人体放电模型 (HBM)	4000	V
	充电器件模型 (CDM)	2000	
$T_J$ 、 $T_{stg}$	工作结温、 贮存温度	- 55 至 150	$^\circ\text{C}$

- (1) 典型  $R_{\theta JA} = 90^\circ\text{C/W}$  (在 0.06 英寸 (1.52mm) 厚的 FR4 PCB 上安装 1 平方英寸 (6.45cm<sup>2</sup>)、2oz、0.071mm 厚的铜焊盘时)。
- (2) 电路板覆铜面积最小时的典型  $R_{\theta JA} = 255^\circ\text{C/W}$
- (3) 脉冲持续时间  $\leq 100 \mu\text{s}$ ，占空比  $\leq 1\%$ 。



顶视图



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## 4 Revision History

<b>Changes from Revision A (August 2017) to Revision B (February 2022)</b>	<b>Page</b>
• 将超薄型封装要点中的厚度从 0.35mm 更改为 0.36mm.....	1
• 添加了覆铜面积最大时的电流和功耗限值.....	1
• 添加了有关覆铜面积最小电路板的脚注.....	1
• 将超薄型封装图片中的厚度从 0.35mm 更新为 0.36mm.....	1
• Changed ultra-low profile image height from 0.35 mm to 0.36 mm.....	8
• Added FemtoFET Surface Mount Guide note.....	9

<b>Changes from Revision * (April 2016) to Revision A (August 2017)</b>	<b>Page</b>
• Added the <a href="#">节 6.1</a> section in <a href="#">节 6</a> .....	7
• Updated the <a href="#">节 7.3</a> .....	9

## 5 Specifications

### 5.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>STATIC CHARACTERISTICS</b>						
$BV_{DSS}$	Drain-to-source voltage	$V_{GS} = 0\text{ V}, I_{DS} = -250\ \mu\text{A}$	-12			V
$I_{DSS}$	Drain-to-source leakage current	$V_{GS} = 0\text{ V}, V_{DS} = -9.6\text{ V}$			-50	nA
$I_{GSS}$	Gate-to-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = -5\text{ V}$			-25	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{DS} = -250\ \mu\text{A}$	-0.40	-0.65	-0.95	V
$R_{DS(on)}$	Drain-to-source on-resistance	$V_{GS} = -1.5\text{ V}, I_{DS} = -0.1\text{ A}$		230	399	m $\Omega$
		$V_{GS} = -1.8\text{ V}, I_{DS} = -0.4\text{ A}$		180	250	
		$V_{GS} = -2.5\text{ V}, I_{DS} = -0.4\text{ A}$		129	165	
		$V_{GS} = -4.5\text{ V}, I_{DS} = -0.4\text{ A}$		97	116	
$g_{fs}$	Transconductance	$V_{DS} = -1.2\text{ V}, I_{DS} = -0.4\text{ A}$		3		S
<b>DYNAMIC CHARACTERISTICS</b>						
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = -6\text{ V},$ $f = 1\text{ MHz}$		180	234	pF
$C_{oss}$	Output capacitance			73	95	pF
$C_{rss}$	Reverse transfer Capacitance			8.5	11.1	pF
$R_G$	Series gate resistance			9		$\Omega$
$Q_g$	Gate charge total (4.5 V)	$V_{DS} = -6\text{ V}, I_{DS} = -0.4\text{ A}$		0.95	1.23	nC
$Q_{gd}$	Gate charge gate-to-drain			0.068		nC
$Q_{gs}$	Gate charge gate-to-source			0.30		nC
$Q_{g(th)}$	Gate charge at $V_{th}$			0.15		nC
$Q_{oss}$	Output charge	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}$		1.07		nC
$t_{d(on)}$	Turnon delay time	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V},$ $I_{DS} = -0.4\text{ A}, R_G = 0\ \Omega$		8		ns
$t_r$	Rise time			4		ns
$t_{d(off)}$	Turnoff delay time			21		ns
$t_f$	Fall time			8		ns
<b>DIODE CHARACTERISTICS</b>						
$V_{SD}$	Diode forward voltage	$I_{SD} = -0.4\text{ A}, V_{GS} = 0\text{ V}$	-0.73		-1.0	V

### 5.2 Thermal Information

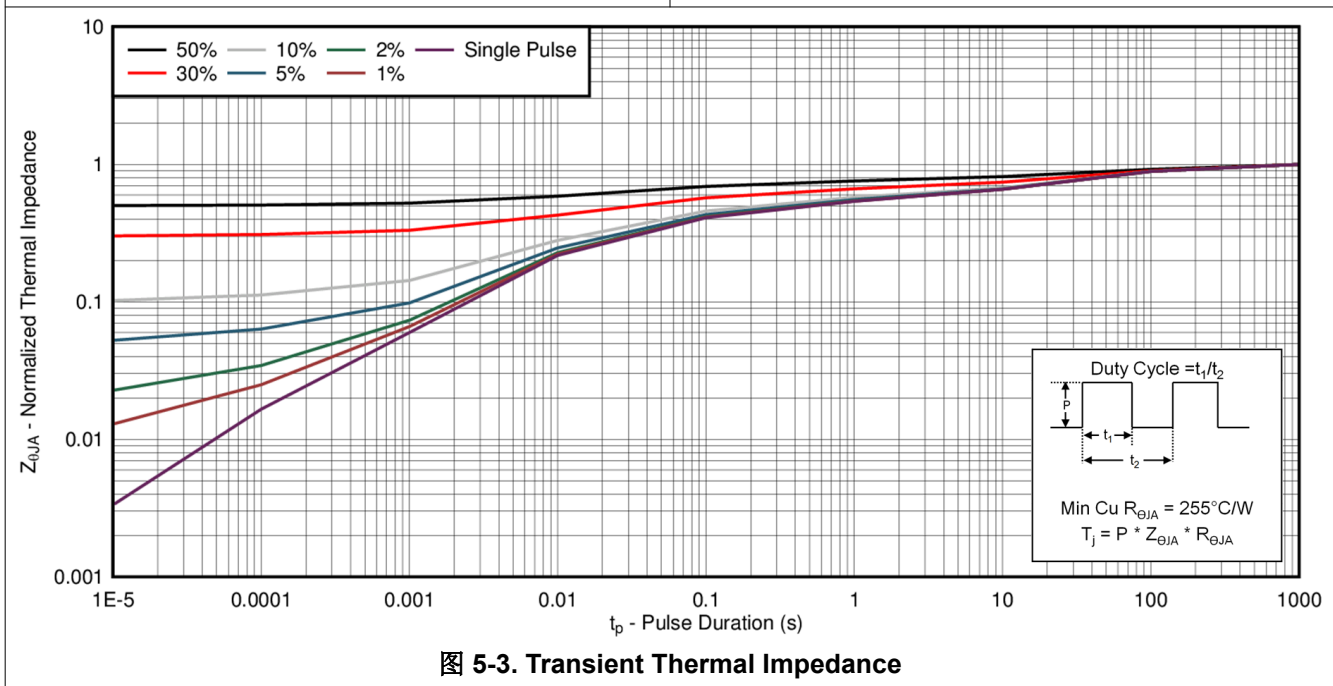
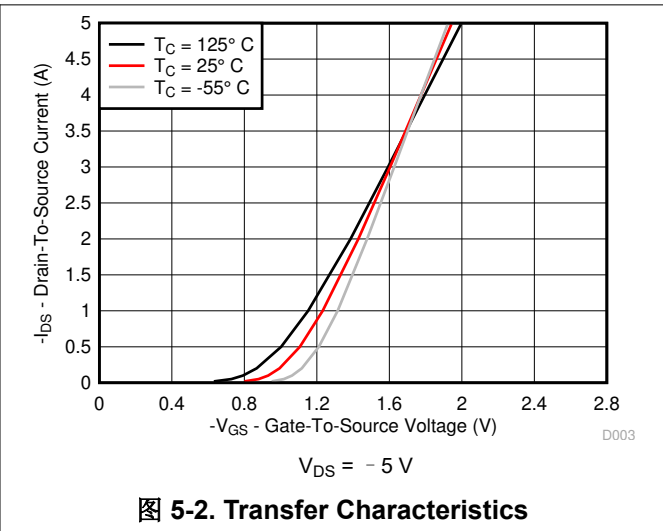
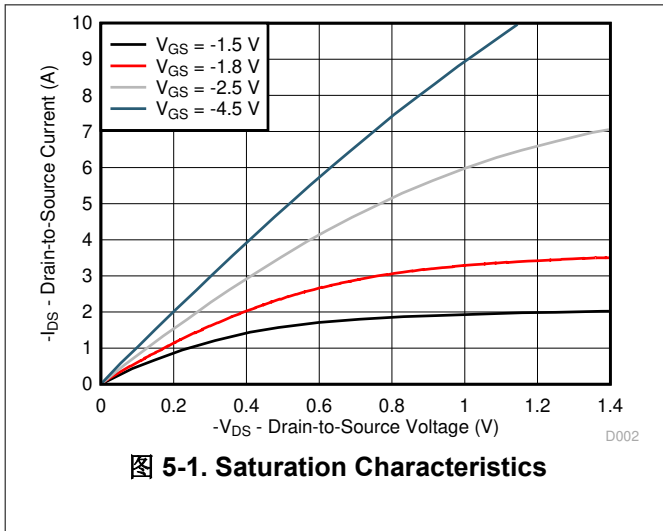
$T_A = 25^\circ\text{C}$  (unless otherwise stated)

THERMAL METRIC		TYPICAL VALUES	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)</sup>	90	$^\circ\text{C/W}$
	Junction-to-ambient thermal resistance <sup>(2)</sup>	255	

- (1) Device mounted on FR4 material with 1-in<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm) thick Cu.  
(2) Device mounted on FR4 material with minimum Cu mounting area.

### 5.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise stated)



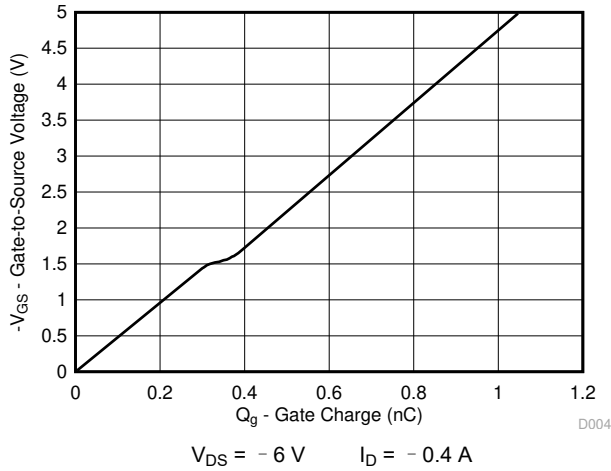


图 5-4. Gate Charge

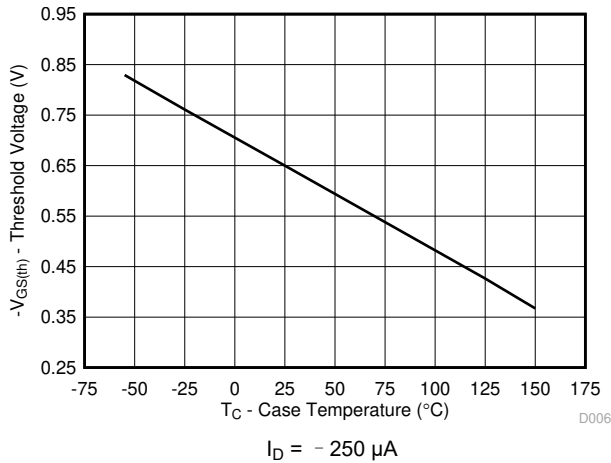
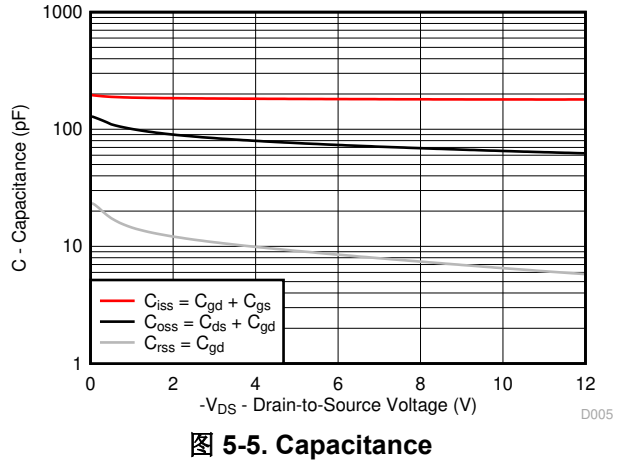


图 5-6. Threshold Voltage vs Temperature

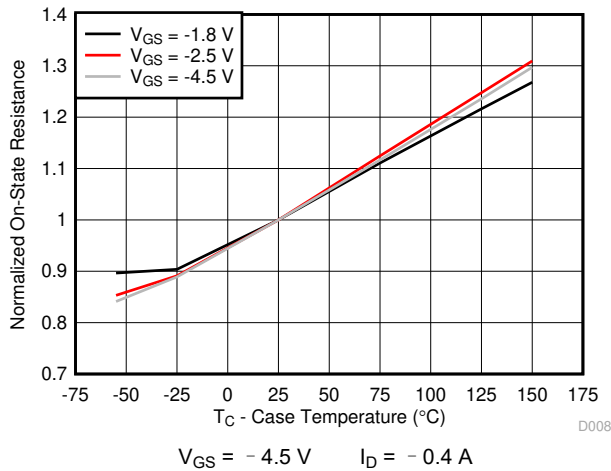
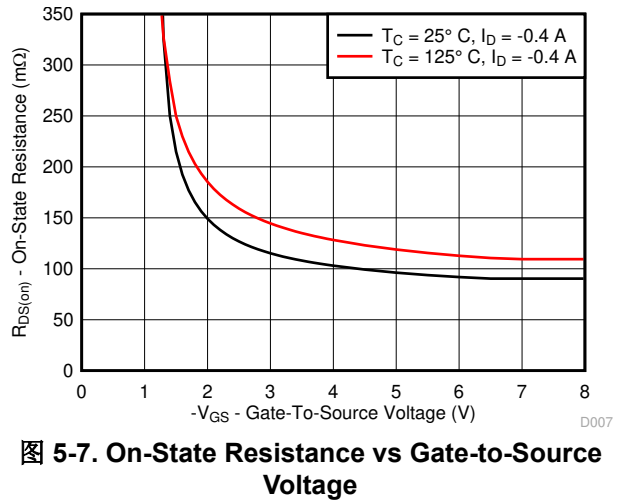
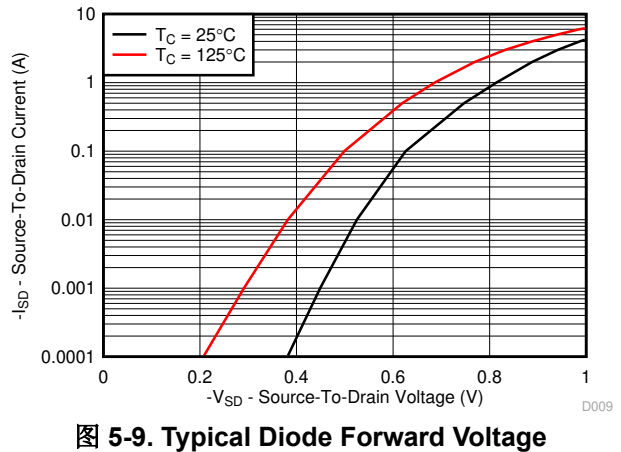


图 5-8. Normalized On-State Resistance vs Temperature



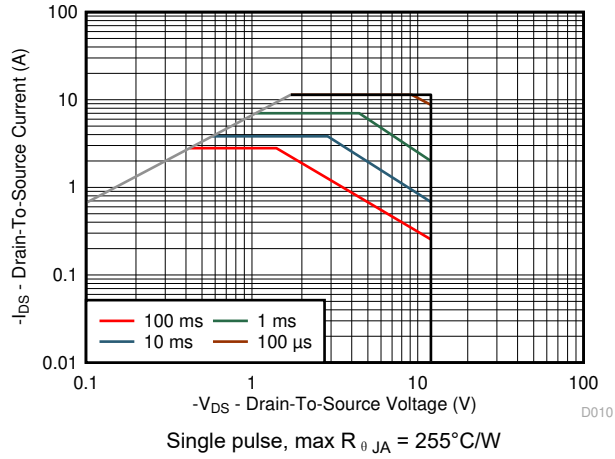


图 5-10. Maximum Safe Operating Area

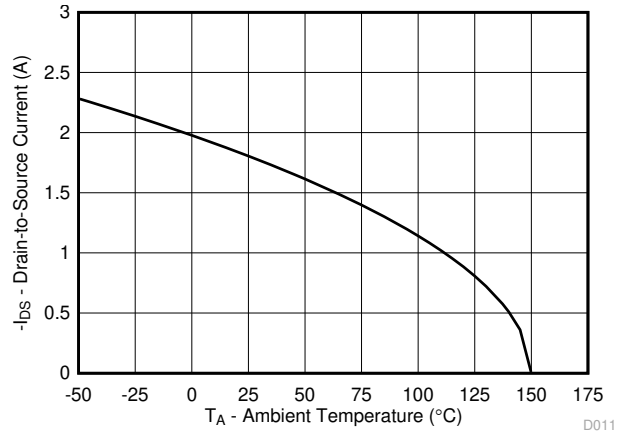


图 5-11. Maximum Drain Current vs Temperature

## 6 Device and Documentation Support

### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

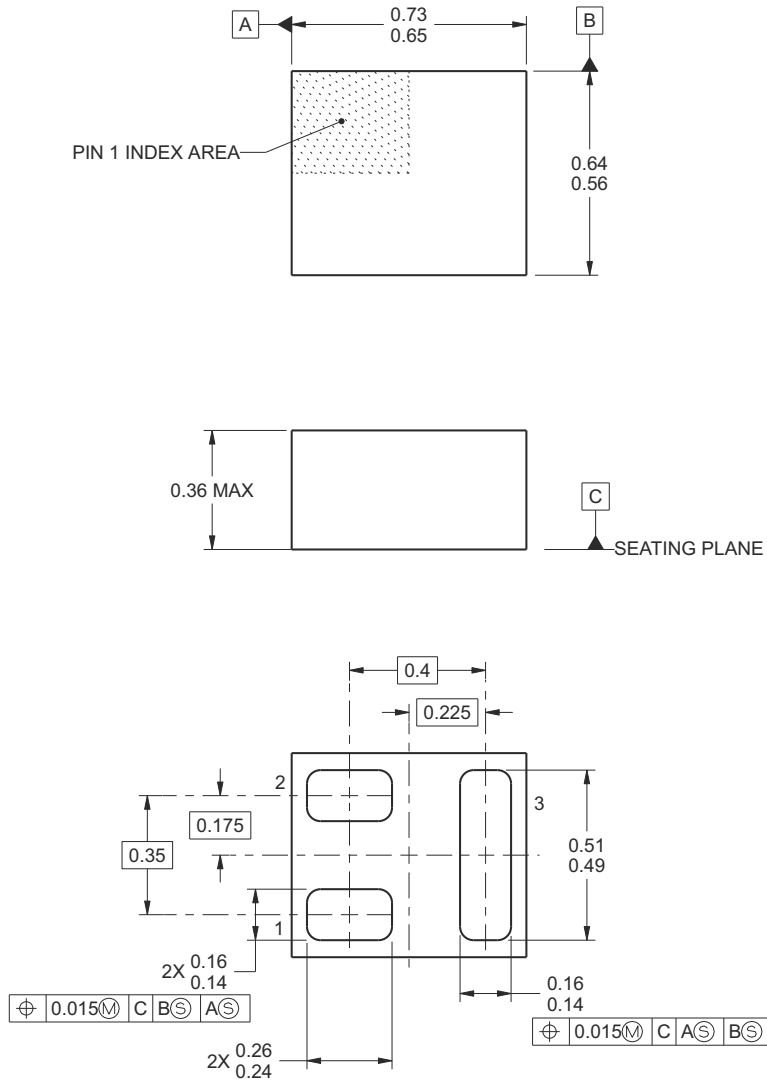
### 6.2 Trademarks

FemtoFET™ is a trademark of Texas Instruments.  
所有商标均为其各自所有者的财产。

## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

### 7.1 Mechanical Dimensions



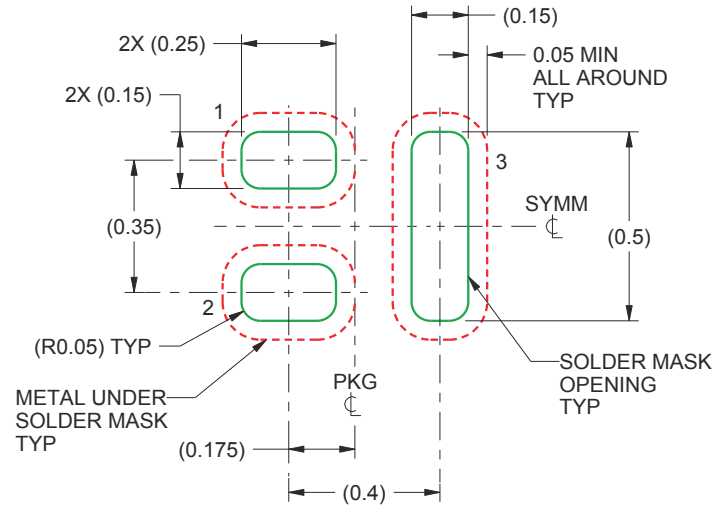
- A. All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- B. This drawing is subject to change without notice.
- C. This package is a lead-free solder land design.

**表 7-1. Pin Configuration**

POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

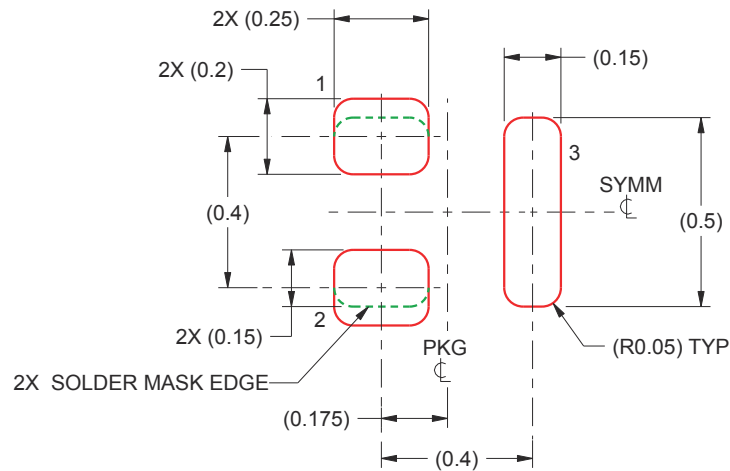


## 7.2 Recommended Minimum PCB Layout



- A. All dimensions are in millimeters.
- B. For more information, see [FemtoFET Surface Mount Guide \(SLRA003D\)](#).

## 7.3 Recommended Stencil Pattern



- A. All dimensions are in millimeters.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD23280F3	ACTIVE	PICOSTAR	YJM	3	3000	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	5	<a href="#">Samples</a>
CSD23280F3T	ACTIVE	PICOSTAR	YJM	3	250	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	5	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD23280F3	PICOSTAR	YJM	3	3000	180.0	8.4	1.94	0.79	0.44	4.0	8.0	Q2
CSD23280F3T	PICOSTAR	YJM	3	250	180.0	8.4	1.94	0.79	0.44	4.0	8.0	Q2

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD23280F3	PICOSTAR	YJM	3	3000	182.0	182.0	20.0
CSD23280F3T	PICOSTAR	YJM	3	250	182.0	182.0	20.0

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